



P-CHANNEL MOSFETS

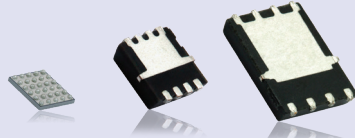
-12 V TO -40 V TrenchFET® GEN III AND IV

IN A NUTSHELL

Breakdown voltages: **-12 V to -40 V**

Industry's lowest $R_{DS(ON)}$
in an array of advanced packages

- Minimize power loss and voltage drop

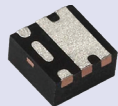


Part #	Si8851EDB	SiSA01DN	Si7155DP
V_{DS}	-20 V	-30 V	-40 V
$R_{DS(ON)}$	< 8 m Ω	< 4.9 m Ω	< 3.6 m Ω
Footprint (mm)	2.4 x 2	3.3 x 3.3	6 x 5

Up to 31 A continuous drain current rating in **2 mm x 2 mm** package

PowerPAK® SC-70

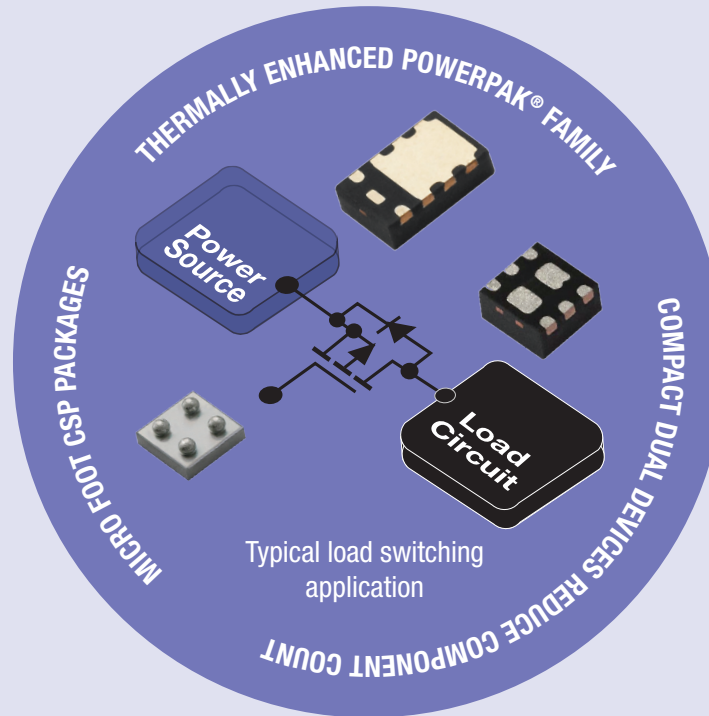
2.05 mm x 2.05 mm x 0.75 mm



Part #	SiA467EDJ	SiA437DJ
V_{DS}	-12 V	-20 V
$R_{DS(ON)}$	< 13 m Ω	< 14.5 m Ω
Continuous I_D	31	29.7

Battery application driven features

- Guaranteed **1.5 V** rated $R_{DS(ON)}$
- **ESD** protection **up to 8 kV (HBM)**



Minimizes Footprint Requirement
Package size down to 0.8 mm x 0.6 mm



MICRO FOOT®
0.8 mm x 0.8 mm



PowerPAK® 0806
0.8 mm x 0.6 mm

Enable **LONGER** battery life



INCREASE efficiency of power delivery

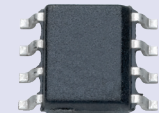
PREVENT undesired fault signals

COMPACT and space saving PCB layout **OPTIMIZATION**



SiSA01DN

-30 V, 4.9 m Ω
PowerPAK® 1212-8
10.89 mm²



SO-8 equivalent

-30 V, 5 m Ω
SO-8
31 mm²

65 % Smaller footprint

APPLICATIONS



BATTERY POWERED EQUIPMENT



NOTEBOOKS / TABLETS



GAME CONSOLES



CONSUMER ELECTRONICS



WEARABLES